



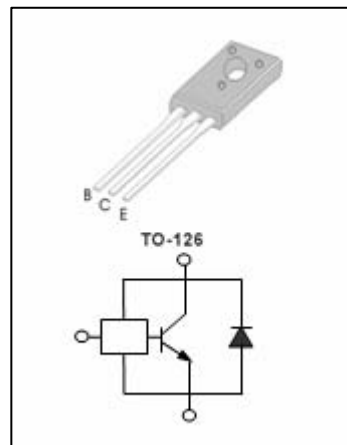
HK13003E

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- **FEATURES:** ■ HIGH VOLTAGE CAPABILITY ■ HIGH SPEED SWITCHING ■ WIDE SOA
- **APPLICATION:** ■ FLUORESCENT LAMP ■ ELECTRONIC BALLAST

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	700	V
Collector-Emitter Voltage	V_{CEO}	480	V
Emitter- Base Voltage	V_{EBO}	9	V
Collector Current	I_C	1.5	A
Total Power Dissipation	P_C	30	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65-150	°C



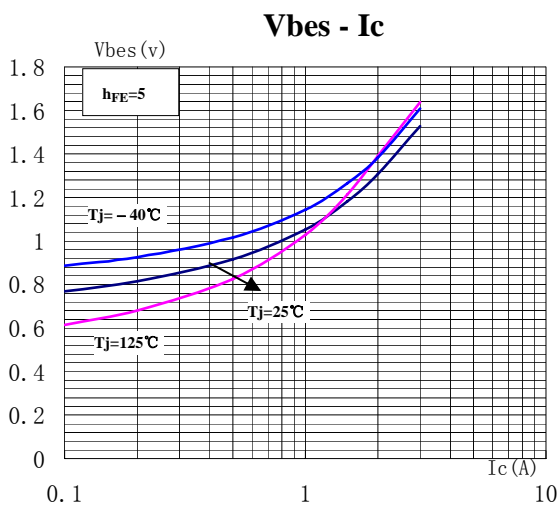
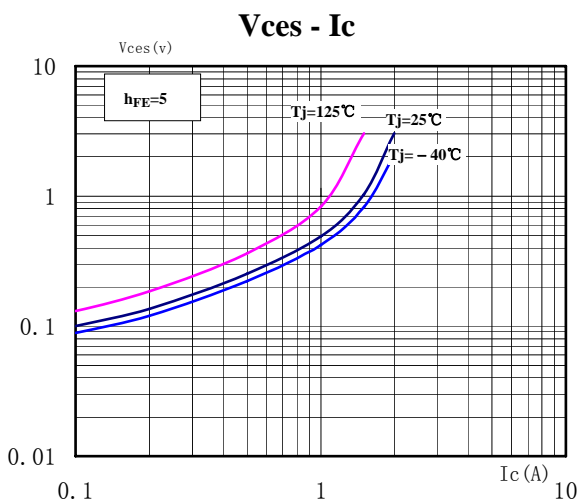
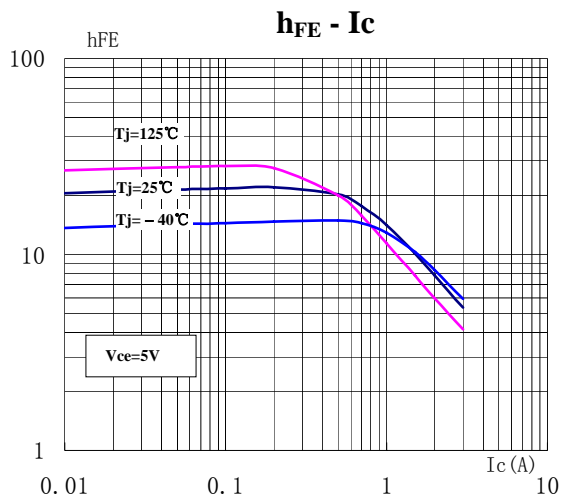
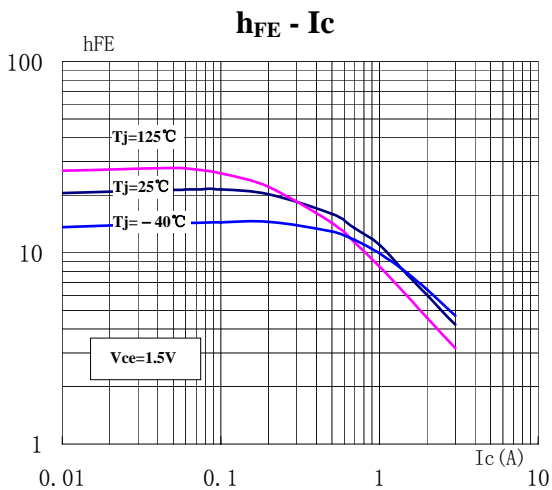
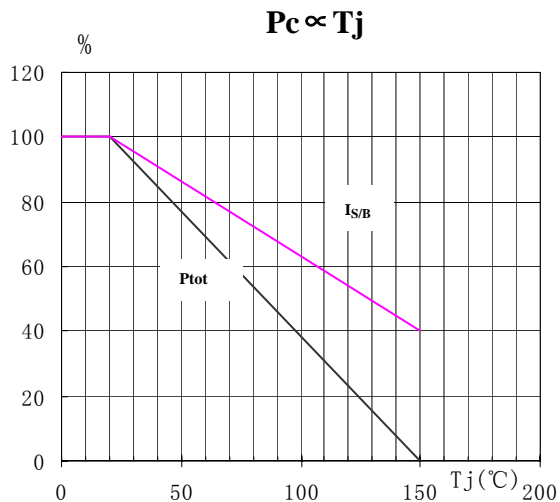
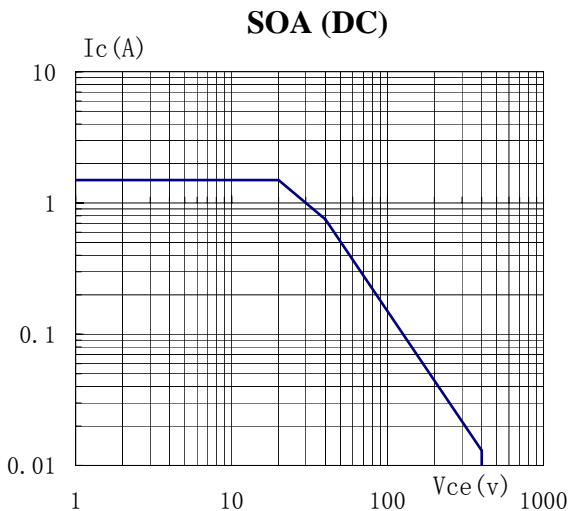
Electronic Characteristics (T_j=25°C Unless OtherWise Specified)

Parameter	Symbol	Test Conditons	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=1mA, I_E=0$	700		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10mA, I_B=0$	480		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1mA, I_C=0$	9		V
Collector-Base Cutoff Current	I_{CBO}	$V_{CB}=600V, I_E=0$		10	μA
Collector-Emitter Cutoff Current	I_{CEO}	$V_{CE}=400V, I_B=0$		20	μA
Emitter –Base Cutoff Current	I_{EBO}	$V_{EB}=9V, I_C=0$		20	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=200mA$	15	30	
DC Current Gain	$h_{FE(2)}$	$V_{CE}=5V, I_C=5mA$	10		
Collector-Emitter Saturation Voltage	V_{CESAT}	$I_C=1.2A, I_B=0.3A$		1.2	V
Base-Emitter Saturation Voltage	V_{BESAT}	$I_C=1.2A, I_B=0.3A$		1.3	V
Storage Time	t_s	UI9600	1.5	3.5	μs
Falling Time	t_f	$I_C=0.25A$		1.0	μs



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TO-126 MECHANICAL DATA

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	2.3		2.8	L	15.3		16.5
B	1.0		1.2	L1			2.54
B1	0.8		1.0	ϕP	3.0		3.2
b	0.65		0.88	$\phi P1$		5.0	
c	0.36		0.60	Q	3.6		4.4
D	10.5		11.1	Q1	0.9		1.5
E	7.2		7.8	R		0.5*	
e		2.29					

